

Silicon PNP Power Transistors

2SB656

DESCRIPTION

- With TO-3 package
- High power dissipation

APPLICATIONS

- For use in power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings($T_a =$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-160	V
V_{CEO}	Collector-emitter voltage	Open base	-160	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-12	A
I_B	Base current		-4	A
P_C	Collector power dissipation	$T_C=25$	125	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -50\text{mA}$; $I_B = 0$	-160			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C = -1\text{mA}$; $I_E = 0$	-160			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E = -1\text{mA}$; $I_C = 0$	-5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C = -10\text{A}$; $I_B = -1\text{A}$			-3.0	V
I_{CBO}	Collector cut-off current	$V_{CB} = -160\text{V}$; $I_E = 0$			-0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB} = -5\text{V}$; $I_C = 0$			-0.1	mA
h_{FE}	DC current gain	$I_C = -1\text{A}$; $V_{CE} = -5\text{V}$	60		200	
f_T	Transition frequency	$I_C = -1\text{A}$; $V_{CE} = -10\text{V}$		20		MHz

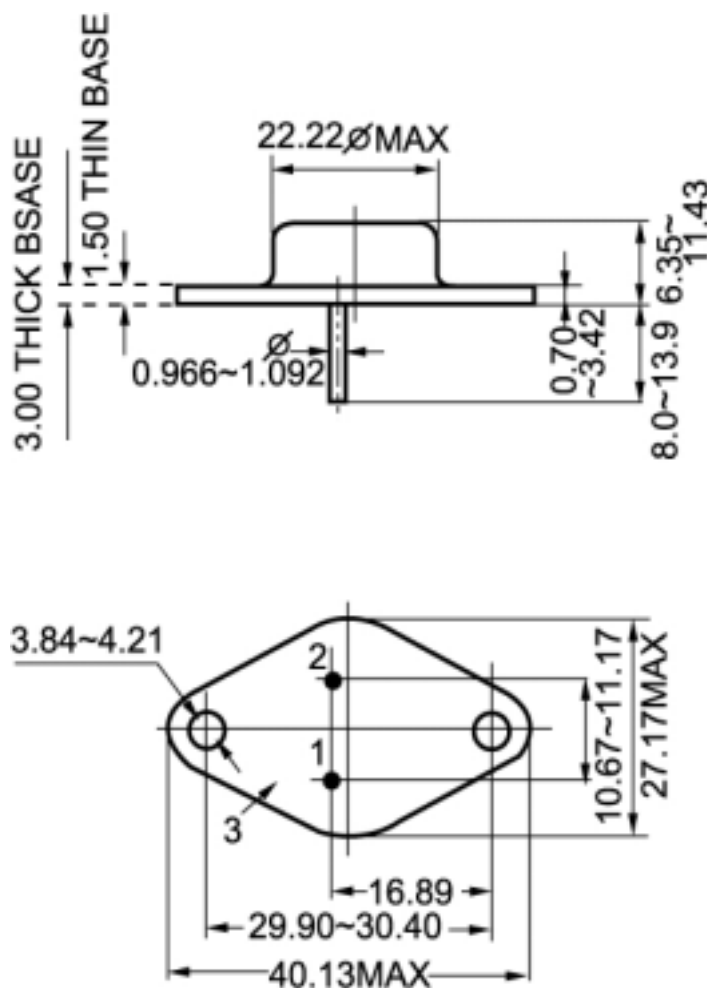
◆ h_{FE} Classifications

B	C
60-120	100-200

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PACKAGE OUTLINE

Fig.2 outline dimensions (unindicated tolerance: $\pm 0.1\text{mm}$)